Anisotropy of superconductivity of as-grown MgB_2 thin films by molecular beam epitaxy

Y. Harada

Advanced Science and Technology Institute of Iwate,

Iwate Industrial Promotion Center,

Iioka shinden 3-35-2, Morioka, 020-0852, Japan

M. Udsuka, Y. Nakanishi, and M. Yoshizawa

Graduate School of Frontier Materials and Functional Engineering, Iwate University,

Ueda 4-3-5, Morioka, 020-8551, Japan

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Abstract

Superconducting thin films of magnesium diboride (MgB_2) were prepared on MgO (001) substrate by a molecular beam epitaxy (MBE) method with the co-evaporation conditions of low deposition rate in ultra-high vacuum. The structural and physical properties of the films were studied by RHEED, XRD, XPS, resistivity and magnetization measurements. All films demonstrated superconductivity without use of any post-annealing process. The highest $T_{c,onset}$ determined by resistivity measurement was about 33K in the present samples. Anisotropic superconducting properties were evaluated by the resistivity and magnetic measurements. We will discuss the anisotropy of superconductivity for as-grown MgB_2 thin films.

INTRODUCTION

The discovery of superconductivity at 39K in magnesium diboride (MgB_2) has attracted great interest in science and technology since it shows the highest transition temperature (T_c) among intermetallic compounds [1]. There have already been several reports on the preparation technique of MgB_2 thin films so far [2, 3]. Many of them require a post-annealing process to improve their physical properties and attain superconductivity. As-grown process without the use of any post-annealing process is strongly desired for the fabrication of tunnelling junctions and multilayers. Several groups have reported as-grown superconducting MgB_2 thin films so far [4, 5, 6]. In as-grown method, low temperature synthesis, is needed to depress high volatility of Mg, makes difficult to produce MgB_2 thin film with high crystallinity. It is considered that MgB_2 needs to be grown up in vacuum as high as possible to get good crystallinity, because the quality of MgB_2 thin film is considerably affected by residual gases [7]. This method is a promising way for device application. Therefore, it is desired to establish the low rate deposition technique at low growth temperature to produce high quality films.

The evaluation of the anisotropy in superconducting materials is very important not only for the basic understanding of this material but also for its potential applications because anisotropy strongly affects the flux pinning, critical currents, and electronic device limit. Since MgB_2 consists of alternating hexagonal layers of Mg atoms and graphite-like honeycomb layers of B atoms, electronic anisotropy has been predicted by theoretical calculations [8, 9]. However, only few indirect measurements have been made to determine the anisotropy, e.g., on single crystal [10], and c-axis oriented thin films of MgB_2 [11]. The anisotropy ratio, $= H_{C2,c}(0)/H_{C2,ab}(0)$, were reported as 2.6 and 1.8–2.0, respectively.

We reported previously the synthesis of thin film by molecular beam epitaxy (MBE) in the co-evaporation conditions of low growth temperature, low deposition rates and ultra high vacuum [12]. In this paper, we present the optimizing of the co-evaporation conditions for as-grown superconducting thin film of MgB_2 using co-evaporation method. And anisotropic superconducting properties were evaluated by the resistivity and magnetic measurements.

EXPERIMENTAL

The MgB_2 films were grown on MgO (001) substrates in an MBE chamber with a base pressure of 4 10^{10} Torr. Pure metal of Mg and B were used as the evaporation sources. The both purities of Mg and B were 3N. Mg was evaporated from a Knudsen cell, and B by electron-beam. The deposition rate was controlled by a quartz-crystal monitor (QCM) with the ux ratio of Mg to B varied from 9 to 10 times as high as the nominal ux ratio to compensate Mg loss. The deposition rate of B was varied from 0.5A/sec to 0.3A/sec. The thickness of lms was typically 1000A. The growth temperature (T_S) was varied from 300 C to 200 C. The background pressure during the growth was better than 4 10^{10} Torr. All of the lms were covered by 50A-thick Mg cap layer to avoid oxidation. The crystal structure was characterized by in-situ re ection high-energy electron di raction (RHEED) and ex-situ X-ray di raction (XRD: 2 scan). The composition of the lms was investigated by X-ray Photoelectron Spectroscopy (XPS). The resistivity and magnetic susceptibility measurements were carried out by the standard four-probe technique and SQUID magnetometer, respectively.

RESULTS AND DISCUSSION

We examined the characteristics of a thin lm made under a range of deposition conditions on a MgO (001) substrate. Firstly, we examined MgB_2 thin lms made by using a relatively low deposition temperature of 100–300 C. The deposition rate of B was xed at 0.5A/sec. Figure 1(a) shows the resistivity as a function of temperature curve of the MgB_2 thin lms grown at 200 C and 250 C with an Mg/B ratio of 9–10. The $T_{c,onset}$–$T_{c,offset}$ was 33.1–31.1K and 31.3–28.3K, respectively. Here, $T_{c,onset}$ was de ned as the temperature at resistance abruptly to drop, and the $T_{c,offset}$ was de ned as the temperature at which resistivity reached zero. The normal state resistivity at room temperature (RT) was 159.5 (250 C) and 93.1 cm (200 C), respectively. It should be marked that the resistivity of the lms grown at 200 C is lower than those of at 250 C. This result can be ascribed to the reduction of grain boundary, that is, enlargement of grain size.

The dc magnetic properties were measured with a superconducting quantum interference device magnetometer (MPMS-5, Quantum design) at an applied eld perpendicular to the

lm plane. The size of samples was 3 3mm^2. Figure 1(b) shows the temperature dependence of the zero- eld-cooled and eld-cooled dc magnetization (M-T) curves of the MgB_2 thin lms grown at 200 C and 250 under a eld of 1m T. The M-T curves exhibit the T_c around 26K (250 C) and 31K (200 C), where the growth temperature are designated in parenthesis.

Figure 2 shows the substrate temperature (T_s) dependence of the T_c. Between 200 C and 250 C, the lms showed superconducting transition above 30K, whereas that made at 300 C showed no superconductivity. This indicates that the growth temperature limit is 300 C for the as-grown superconducting MgB_2 thin lms by these co-evaporation conditions. From these results, we have chosen the typical growth conditions as T_s= 200 C.

To establish optimal conditions, we studied the dependence of B deposition rate on the lm properties. In this series of lms, the growth temperature was xed at 200C. The B deposition rate was decreased from 0.5 to 0.1A/sec to get lower vacuum conditions. The Mg/B ratio was xed at 9-10.

Figure 3(a) shows the resistivity as a function of temperature curve at various B deposition rates. The $T_{c,onset}$-$T_{c,offset}$ was 31.3-28.1K (0.5A/sec), 32.6-31.9K (0.3A/sec) and 30.6-26.2 (0.1A/sec), respectively. The parenthesis mean the B deposition rates. The transition width (T_c) at 0.3A/sec had a very low value of 0.7K. In 0.1A/sec, a clear step like transition were found. This pattern suggests that the possibility of two di erent MgB_2 phase exists in this lm.

Figure 3(b) shows the M-T curves, which B deposition rate was 0.3 and 0.5A/sec. The M-T curves exhibit the T_c around 30K. As these results, the quality and superconducting properties of MgB_2 thin lm made at 0.3A/sec were improved than other deposition rate lms. Therefore, we have chosen the typical growth conditions; B deposition rate: 0.3A/sec.

Next, we studied anisotropy of superconductivity of as-grown MgB_2 thin lm. New lm was prepared at T_s= 200, B deposition rate of 0.3A/sec and Mg deposition rate of around 3A/sec. The structure and crystallinity were characterised by RHEED and XRD. Figure 4(a) shows the XRD pattern of the MgB_2 thin lm. XRD results show the (001) di raction peak of the MgB_2. The RHEED pattern showed a ring pattern. The composition of the lms was investigated by XPS. From the XPS depth pro le shown in Figure 5, it was found that a MgB_2 thin lm is slightly Mg de cient (i.e., 25.0% Mg and 71.3% B).

The dc magnetic properties were studied with a superconducting quantum interference device magnetometer (MPMS-5. Quantum Design) at an applied eld parallel (Hkc) or the

perpendicular to the lm plane (H kab). Figure 6(a) shows M-T curves of the MgB$_2$ thin lm under a eld of 1mT along the perpendicular to the lm plane. The M-T curves exhibit the same superconducting transition temperature of T_C around 31K. The magnetization of the thin lm, as a function of an applied eld up to 3T (M-H curve), was measured at several temperatures. Figure 6(b) shows the M-H curves at 5K for applied elds up to 3T at H kc and H kab. They show the typical hysteresis loop, indicating the characteristic curve of type-II superconductors. M-H curves exhibit a remarkable anisotropy between parallel and perpendicular to the lm plane.

To estimate the critical current density (J_C), we measured M-H curves of the same samples as a function of temperature. The J_C was calculated based on the Bean model [13], $J_C = 30\ m\ V^{-1}\ r^{-1}$, where m is the width of the hysteresis loop, V is the lm volume, and r is the sample half-width. At zero eld, the $J_{C,c}$ was estimated to be 7.1 10^7A/cm^2 at 5K and 5.1 10^7A/cm^2 at 20K, respectively from the M-H curves of H kc. The $J_{C,ab}$ was 4.7 10^6A/cm^2 at 5K and 3.2 10^6A/cm^2 at 20K, respectively from the M-H curves of H kab. Here, the sample size was employed for the calculation of J_C, instead of the grain size.

Figure 7 shows the temperature dependence of the resistivity under the selected magnetic elds up to 14T for H kc and H kab. The $T_{C,onset}$ is estimated to be 31.2K at 0T, which is consistent with the result of M-T measurements. The transition width gradually becomes broader with increasing magnetic eld from about 1K in 0T to 6.0K in 12T. This broadening is smaller compared to previous reported one of MgB$_2$ wires [14], bulk samples [15], or thin lms [5].

From the M-H curves, the lower critical elds, H_{C1} for H kc and H kab, were dened by the magnetic elds where the initial slope of M_{up} curve meets the extrapolated curve of $(M_{up} + M_{down})/2$. The temperature dependence of H_{C1} is plotted as shown in Figure 8. Extrapolation of the plot to zero temperature gives the $H_{C1,c}(0)$ values of 14mT. This $H_{C1}(0)$ gives the penetration depth of 21.7nm at zero temperature based on Ginzburg-Landau (GL) formulas, $H_{C1} \propto {}_0 / {}^2$.

The H_{C2} for H kc and H kab, were determined by the resistive onset temperature in the Figure 7. The $H_{C2}(T)$ curves for H kc and H kab show a linear behavior in the temperature region far from T_C. These results give an approximate slope at T_C of $dH_{C2}/dT = 0.61$ (perpendicular) and 1.1 (parallel) T/K determined from the onset. Therefore, a linear extrapolation to zero

temperature gives the $H_{C2,c}(0)$ and $H_{C2,ab}(0)$ values of 19.6T and 34.5T, respectively. Assuming the dirty limit of the type-II superconductor, the $H_{C2}(0)$ values [16] is expressed as $H_{C2}(0)$ $0.691 |dH_{C2}/dT|_{T_C}$. Thus, $H_{C2,c}(0)$ and $H_{C2,ab}(0)$ are estimated to be 13.2T and 23.6T, respectively. The present values of $H_{C2}(0)$ in MgB_2 thin films are larger than previous ones, for example, grown by the two-step method [3] and reported as-grown method [5]. Using the anisotropic GL formulas: $H_{C2,c}$= /(2 $_{ab}^2$) and $H_{C2,ab}$= /(2 $_{ab}$ $_c$), the GL coherence length $_c(0)$ and $_{ab}(0)$ at zero temperature were calculated to be 2.8nm and 5.0nm, respectively. These values are larger than the typical values observed for high-temperature superconductors (HTS) and comparable to those estimated from the high-pressure sintered polycrystalline sample [1] and single crystal [10]. From the upper critical field H_{C2}, the anisotropy ratio [$= H_{C2,ab}(0)/H_{C2,c}(0)$] was estimated to be 1.78, that is an anisotropy of the coherence length $_{ab}(0)/$ $_c(0)$ 1.78. This value of is comparable to the reported value of 1.8-2.0 for the c-axis oriented MgB_2 thin films by two-step method [11]. The important physical values, H_{C2}, , J_C, H_{C1}, and of our films are summerized in Table 1.

In summary, we have grown the as-grown MgB_2 thin films on MgO (001) substrate by MBE in the conditions of low temperature, low deposition rate and ultra-high vacuum. Currently, B deposition rate is 0.3A/sec and growth temperature is 200 C are best conditions to make the high quality MgB_2 thin film. The films exhibit clear (001) peaks of MgB_2. However, the composition is not yet good enough to get perfectly stoichiometric films. A superconducting transition with the onset temperature around 32K was confirmed through the resistivity and magnetization measurements. We evaluated upper critical field anisotropy ratio of as-grown MgB_2 thin films for the first time. The upper critical field anisotropy ratio of as-grown MgB_2 thin film, $= H_{C2,ab}(0)/H_{C2,c}(0)$ of 1.78, was estimated from the magnetic field-temperature phase diagram for the first time. The observed anisotropy is comparable to the values observed for MgB_2 thin films by two-step method and single crystal These results demonstrated that this as-grown MgB_2 thin film using MBE would be promising for the device application.

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TABLE I: Superconducting properties of as-grown MgB_2 thin films in this work

$H_{C2,c}$		19.6T
$H_{C2,ab}$		34.5T
$H_{C2,c}$ (dirty limit)		13.2T
$H_{C2,ab}$ (dirty limit)		23.6T
$_c(0)$		2.8nm
$_{ab}(0)$		5.0nm
$J_{C,c}(5K)$	7.1	$10^7 A=cm^2$
$J_{C,ab}(5K)$	4.7	$10^6 A=cm^2$
$H_{C1,c}$		14m T
$_c$		21.7nm

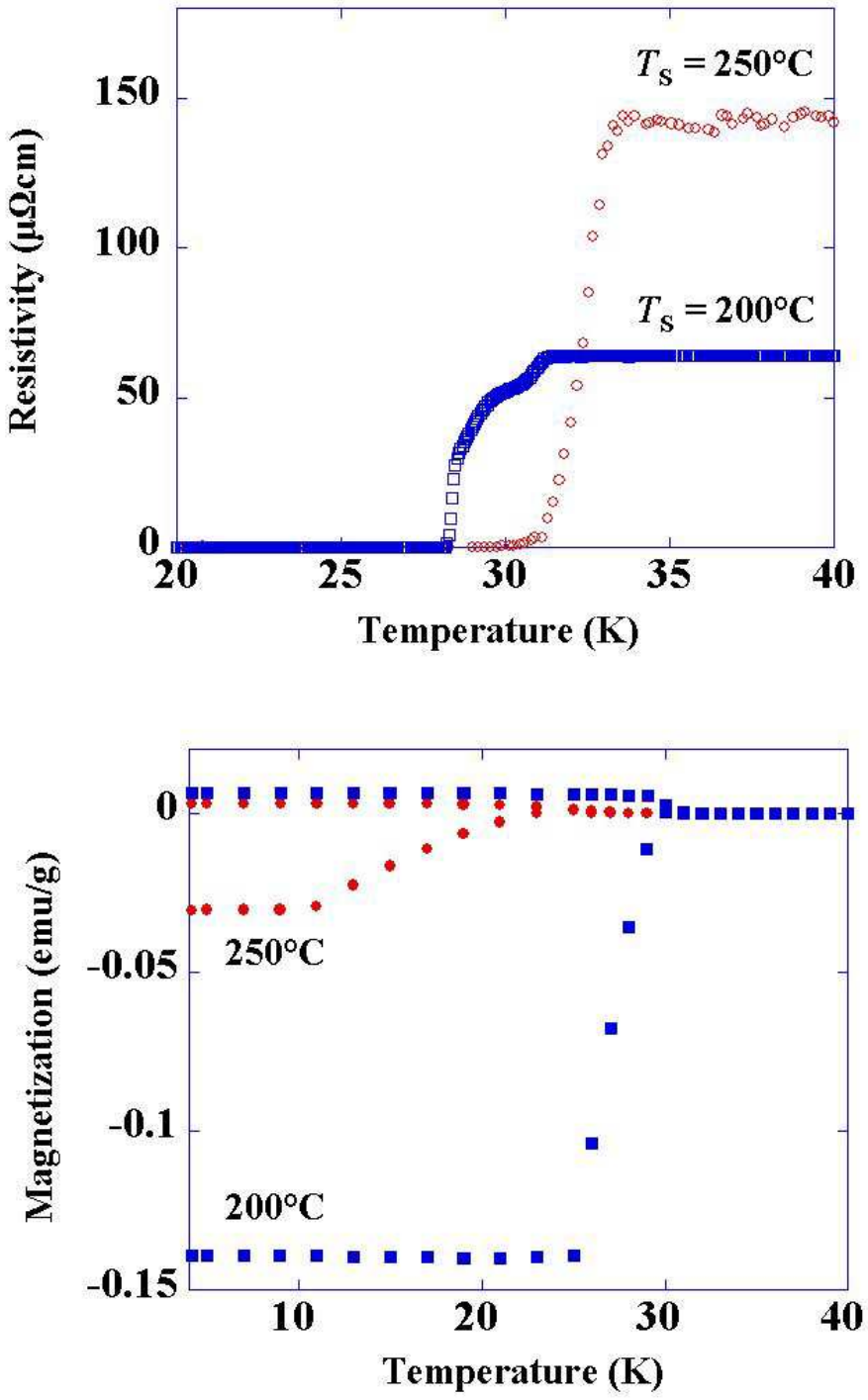

FIG. 1: (a) Resistivity as a function of temperature of MgB_2 thin films grown at 250 C and 200 . (b) Magnetization of these films as a function of temperature after cooling under zero field and under a field of 1m T.

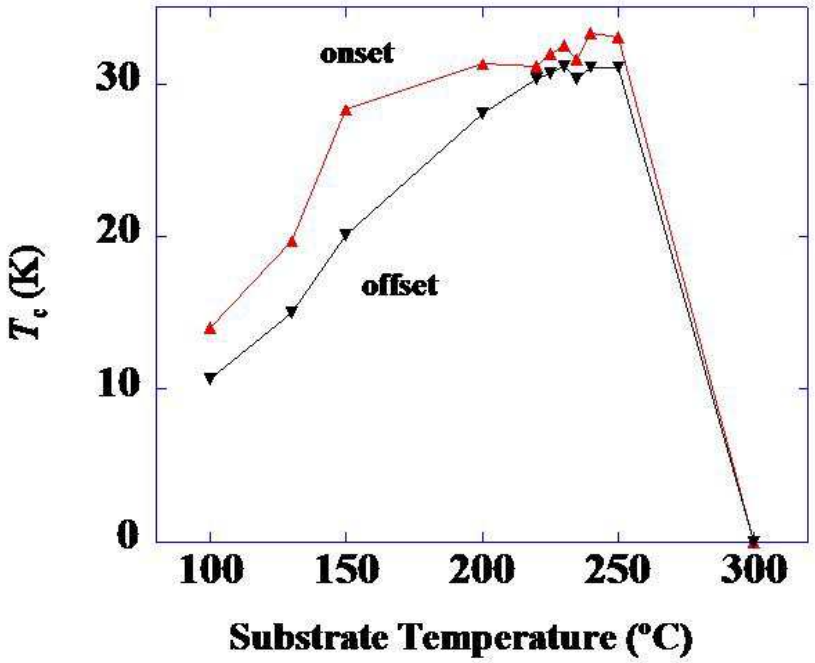

FIG. 2: Substrate temperature dependence of critical temperature. B deposition rate: 0.5A/sec, Mg deposition rate: 4.3A/sec

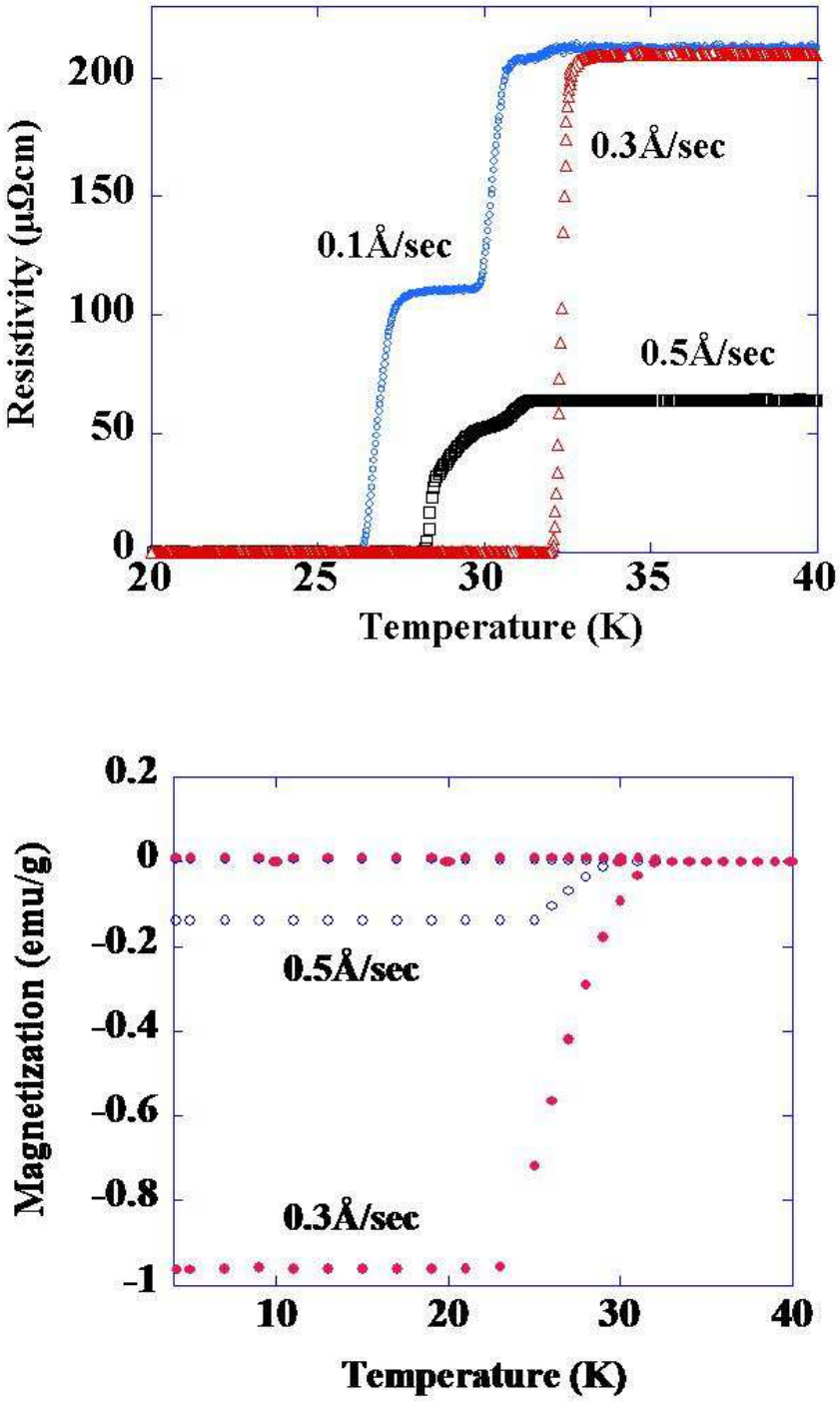

FIG. 3: (a) Resistivity as a function of temperature of MgB_2 thin films under B deposition rates of 0.1, 0.3 and 0.5A/sec. Substrate temperature was fixed at 200 C. (b) Magnetization as a function of temperature under B deposition rate 0.3 and 0.5A/sec.

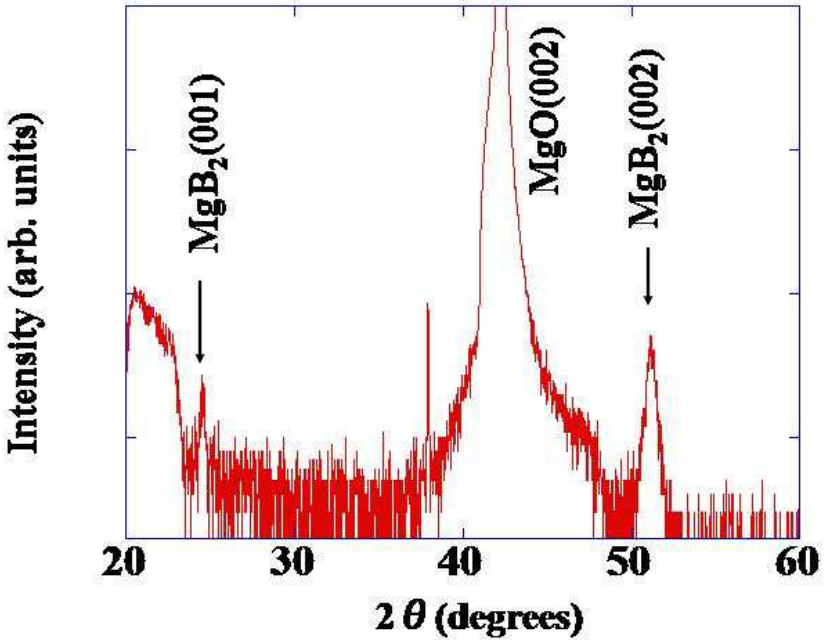

FIG. 4: (a) XRD pattern for MgB_2 thin films grown on MgO (001) substrate.

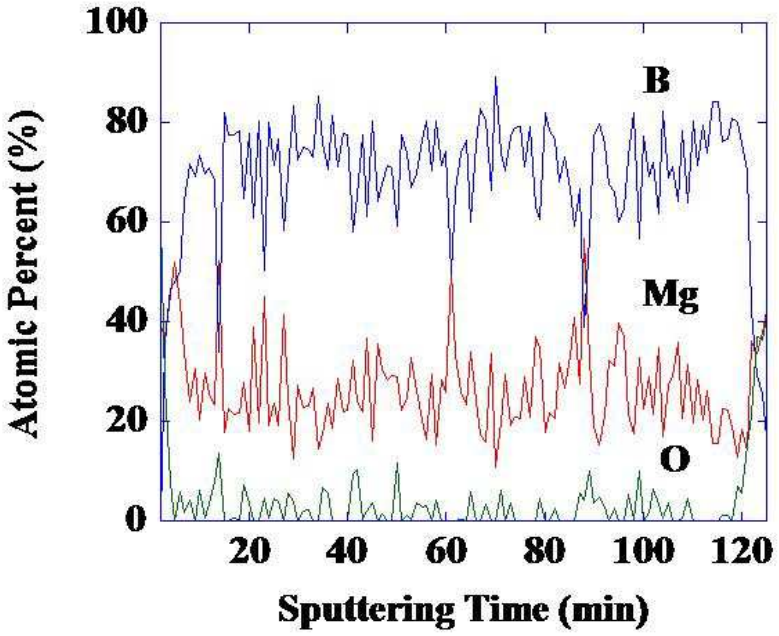

FIG. 5: XPS depth profiles of a MgB_2 film, Mg-cap layer was deposited on the surface MgB_2 thin films.

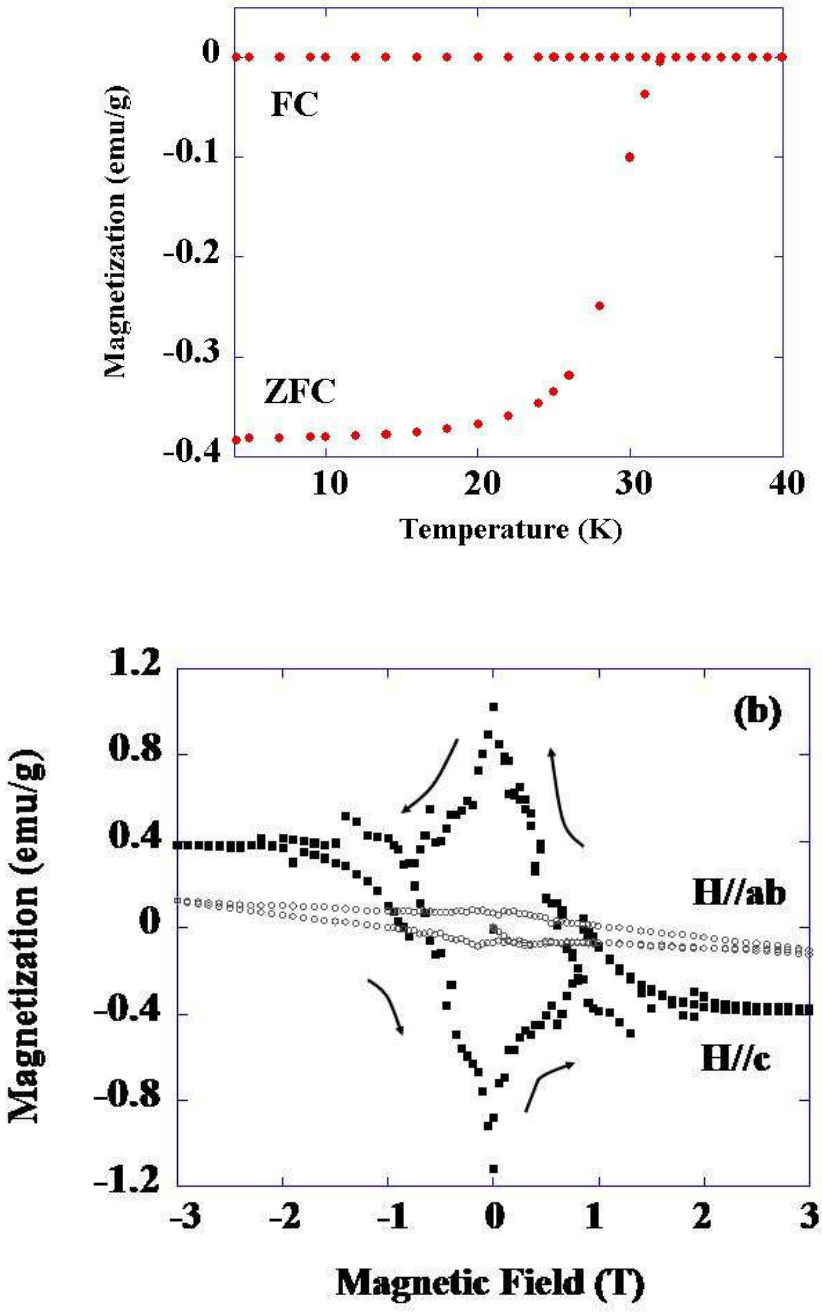

FIG. 6: Magnetic properties of the MgB_2 thin film. (a) Magnetization as a function of temperature after cooling under zero field and under a field of 1mT at H⊥c. (b) Magnetization as a function of applied fields up to 3T at 5K for H⊥c and H∥ab.

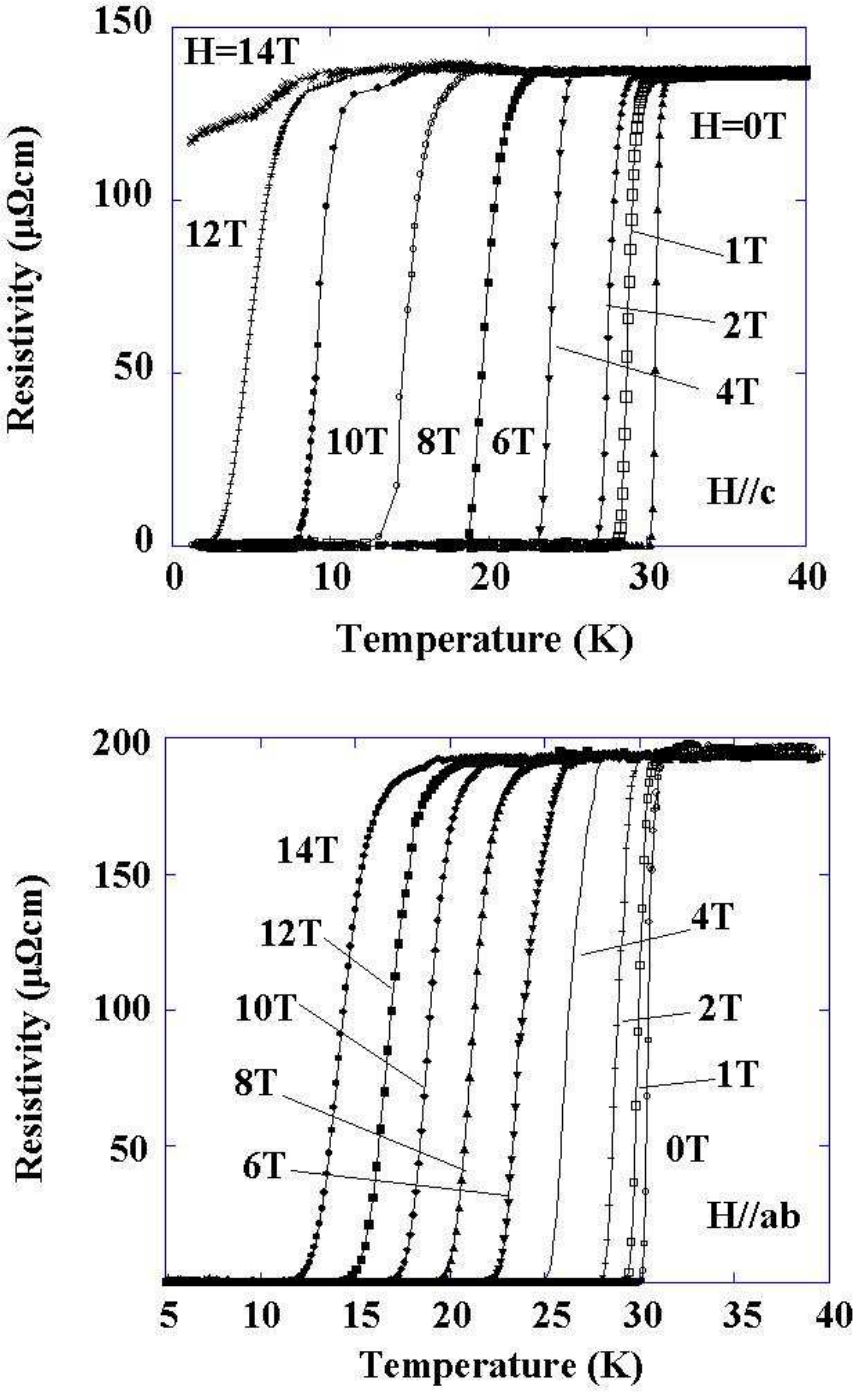

FIG. 7: Resistivity as a function of temperature under selected magnetic fields up to 14T for (a) H kc and (b) H kab.

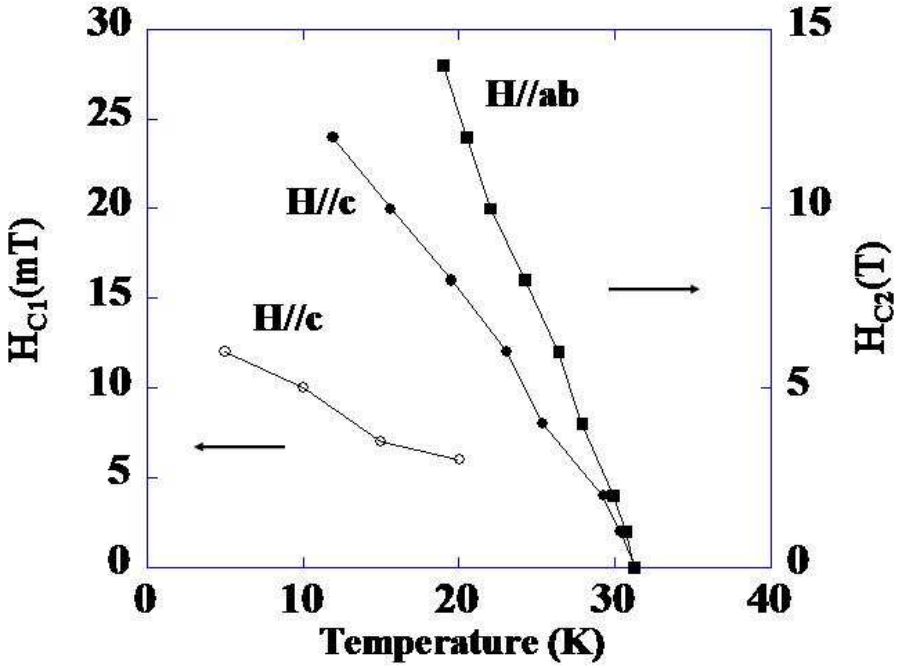

FIG. 8: Magnetic field-temperature phase diagram of the as-grown MgB_2 thin film determined our transport and magnetization experiments.